

REMARKS

This is in response to the Office Action dated March 25, 2004. New claims 21-26 have been added. Thus, claims 1-8 and 15-26 are now pending.

Claim 1 - - Section 103(a) Art Rejection

Claim 1 stands rejected under 35 U.S.C. Section 103(a) as being allegedly unpatentable over Krames in view of Saeki and Vakhshoori. This 3-way Section 103(a) rejection is respectfully traversed for at least the following reasons.

Claim 1 requires "a DBR (Distributed Bragg Reflector) and a light-emitting layer supported by at least a substrate comprising GaAs, the DBR being located between the substrate comprising GaAs and the light-emitting layer, wherein light directed from the light-emitting layer toward a top surface of the light-emitting device has a radiation angle dependence; a semiconductor layer formed over at least the light-emitting layer, a top surface of the semiconductor layer comprising a roughened surface which is not at least partially covered by the other semiconductor layers in order to cause light output from the light-emitting device to be diffused upon leaving the top surface of the device; and wherein no DBR is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened."

Vakhshoori is entirely unrelated to the invention of claim 1. In particular, claim 1 as amended requires that the top surface of the semiconductor layer is at least partially roughened in a manner which causes "light output from the light-emitting device to be diffused upon leaving the top surface of the device." Vakhshoori teaches the opposite of

claim 1 in this respect. Instead of causing output light to be diffused as called for in claim 1, Vakhshoori uses a type of roughness for the express purpose of causing output light to be focused (see Fig. 2; col. 1, lines 50-55; and col. 3, line 55). Thus, it can be seen that Vakhshoori teaches directly away from the invention of claim 1 and is unrelated to the same.

Furthermore, the Examiner's allegation regarding a mirror function teaching of Vakshoori in the Office Action is incorrect. In particular, the Office Action states that Vakshoori teaches that a mirror function can be obtained by a single layer (citing column 3, line 4), so that substitution of a DBR of Krames by a single layer would have been obvious. The Examiner's interpretation of Vakshoori is wrong in this respect. In contrast to the incorrect statements in the Office Action, the mirror function cannot be obtained by a single layer as alleged by the Examiner because a p-type AlGaAs upper mirror (12) is also disclosed at col. 3, line 8, as clearly shown in Fig. 1. In other words, to achieve a mirror, Vakshoori requires both a lower mirror layer of n+ AlGaAs (col. 3, line 4) and an upper mirror layer of p-type AlGaAs (col. 3, line 8). A single layer cannot achieve mirror functionality in Vakshoori. Thus, in direct contrast to the Examiner's unsupported allegation, the mirror function in Vakshoori is achieved by a pair of mirrors – not a single mirror. This means that the device of Vakshoori is an RCLED which is the opposite of what the invention of claim 1 requires. The very basis of the Section 103(a) rejection is based on a misunderstanding of the cited art, thereby evidencing that the Section 103(a) rejection is incorrect and should be withdrawn.

The Office Action also relies on Fig. 13 of Krames. However, in direct contrast to claim 1, the device shown in Fig. 13 of Krames is an RC (Resonance Cavity)-LED necessarily having by definition both an upper DBR (20B) and a lower DBR (20A) (col. 9, lines 5-15). Contrary to what is alleged in the Office Action, one of ordinary skill in the art would never even consider removing the upper DBR from Fig. 13 of Krames as alleged in the Office Action, because this upper DBR is an absolute requirement of the device and its removal would destroy the functionality of the device. In other words, one of ordinary skill in the art would never have removed the upper DBR from Fig. 13 of Krames as alleged in the Office Action, because this would destroy the functionality and operation of Krames' RCLED.

The Office Action also contends that it would have been obvious to have "texture[d] the top surface of the device of Saeki Fig. 8B as taught by Krames et al. with respect to figure 13." This contention is respectfully traversed. The device of Saeki is designed to reduce the operation voltage and increase optical output. To achieve this, a contact layer (22) doped with carbon for reducing the contact resistance with ITO electrode (16) is provided and an intermediate band gap layer (21) is interposed between the contact layer (22) and the cladding layer (15) for alleviating band discontinuity, thereby promoting inflow of holes and decreasing resistance. Consequently, these the need is met by the use of such layers and there would have been no need to further enhance light emission by texturing the top surface of the device.

Moreover, the ordered textures of Krames Fig. 13 are designed to efficiently couple emitted light into ambient (col. 9, lines 5-10), which is much different than the diffusing/scattering function required by claim 1. The Examiner relies on Fig. 13 of Krames for alleged diffusion. In particular, the Examiner has contended that "diffusion, or spreading out, of the emission profile is shown in Figure 13 of Krames et al., for example, where the lobes of the profile indicate the spread." *The Examiner has misinterpreted Krames in this regard*; Krames discloses no such diffusion. In particular, the lobes in Krames indicate only the spreading spectrum of the emitted light from the active region (2) and they are not diffused because they have not yet reached the surface. Again, the basis of the Section 103(a) rejection is incorrect, thereby evidencing that the Section 103(a) rejection is incorrect and should be withdrawn.

For at least the aforesaid reasons, it is respectfully requested that the rejection of claim 1 be withdrawn.

Claim 15

Claim 15 states that "a roughened surface which is not at least partially covered by the other semiconductor layers in order to cause light output from the light-emitting device to be diffused upon leaving the top surface of the device; and wherein no DBR is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened." The cited art fails to disclose or suggest these aspects of amended claim 15.

Claims 25-26

Claims 25-26 require that "no mirror/reflector is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened."

The cited art fails to disclose or suggest this.

The Office Action contends that it would have been obvious to have replaced the upper DBR of Krames with the mirror/reflector of Vakhshoori (this alleged modification has been traversed above). However, even if this modification were made, the inventions of claims 25-26 still would not be met. There would still be a reflector between the light emitting layer and the roughened surface, which is expressly excluded by these claims. Thus, even the alleged combination set forth in the Office Action fails to meet the inventions of claims 25-26.

Claims 8, 21-22

Claims 21-22 require that "the semiconductor with roughened surface has a lattice constant different by 0.5% or more than that of the substrate comprising GaAs." The cited art fails to disclose or suggest this aspect of these claims.

The instant specification explains that this lattice constant difference of 0.5% or more is highly advantageous in that it allows the wafer surface to be roughened by a sequence of crystal growth due to the lattice constant difference, thereby permitting a step of separately roughening the surface after crystal growth to be eliminated (e.g., pg. 8, lines 3-10; pg. 11, lines 5-18). The cited art fails to disclose or suggest the aforesaid quoted aspect of claims 21-22. Claim 8 defines over the cited art in a similar manner.

Claims 23-24

Claims 23-24 require that the "top electrode of the device includes a plurality of separate apertures defined therein so as to expose different parts of the roughened surface of the semiconductor layer." For example, see Fig. 2A of the instant application. The cited art fails to disclose or suggest this aspect of claims 23-24.

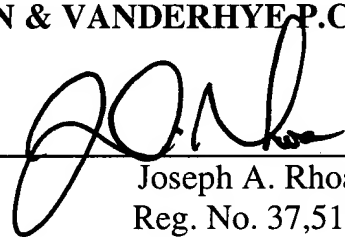
Conclusion

For at least the foregoing reasons, it is respectfully requested that all rejections be withdrawn. All claims are in condition for allowance. If any minor matter remains to be resolved, the Examiner is invited to telephone the undersigned with regard to the same.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: _____



Joseph A. Rhoa
Reg. No. 37,515

JAR:caj
1100 North Glebe Road, 8th Floor
Arlington, VA 22201-4714
Telephone: (703) 816-4000
Facsimile: (703) 816-4100